

STARPOWER

SEMICONDUCTOR

IGBT

GD200HFX65C2S

650V/200A 2 in one-package

General Description

STARPOWER IGBT Power Module provides ultra low conduction loss as well as short circuit ruggedness. They are designed for the applications such as general inverters and UPS.

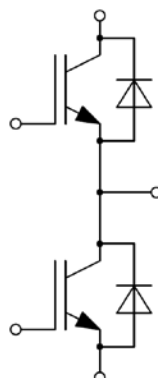
Features

- Low $V_{CE(sat)}$ Trench IGBT technology
- 6 μ s short circuit capability
- $V_{CE(sat)}$ with positive temperature coefficient
- Maximum junction temperature 175°C
- Low inductance case
- Fast & soft reverse recovery anti-parallel FWD
- Isolated copper baseplate using DBC technology

Typical Applications

- Automotive application
- Hybrid and electric vehicle
- Inverter for motor drive

Equivalent Circuit Schematic



Absolute Maximum Ratings $T_C=25^{\circ}\text{C}$ unless otherwise noted**IGBT**

Symbol	Description	Value	Unit
V_{CES}	Collector-Emitter Voltage	650	V
V_{GES}	Gate-Emitter Voltage	± 20	V
I_C	Collector Current @ $T_C=25^{\circ}\text{C}$ @ $T_C=65^{\circ}\text{C}$	247 200	A
I_{CM}	Pulsed Collector Current $t_p=1\text{ms}$	400	A
P_D	Maximum Power Dissipation @ $T_j=175^{\circ}\text{C}$	612	W

Diode

Symbol	Description	Value	Unit
V_{RRM}	Repetitive Peak Reverse Voltage	650	V
I_F	Diode Continuous Forward Current	200	A
I_{FM}	Diode Maximum Forward Current $t_p=1\text{ms}$	400	A

Module

Symbol	Description	Value	Unit
T_{jmax}	Maximum Junction Temperature	175	$^{\circ}\text{C}$
T_{jop}	Operating Junction Temperature	-40 to +150	$^{\circ}\text{C}$
T_{STG}	Storage Temperature Range	-40 to +125	$^{\circ}\text{C}$
V_{ISO}	Isolation Voltage RMS, $f=50\text{Hz}$, $t=1\text{min}$	4000	V

IGBT Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$V_{CE(sat)}$	Collector to Emitter Saturation Voltage	$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=25^{\circ}\text{C}$		1.45	1.90	V
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=125^{\circ}\text{C}$		1.60		
		$I_C=200\text{A}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}$		1.70		
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C=3.2\text{mA}, V_{CE}=V_{GE}, T_j=25^{\circ}\text{C}$	5.1	5.8	6.5	V
I_{CES}	Collector Cut-Off Current	$V_{CE}=V_{CES}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$			1.0	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE}=V_{GES}, V_{CE}=0\text{V}, T_j=25^{\circ}\text{C}$			400	nA
R_{Gint}	Internal Gate Resistance			2.0		Ω
C_{ies}	Input Capacitance	$V_{CE}=25\text{V}, f=1\text{MHz}, V_{GE}=0\text{V}$		23.2		nF
C_{res}	Reverse Transfer Capacitance			0.46		nF
Q_G	Gate Charge	$V_{GE}=-15\dots+15\text{V}$		1.39		μC
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}, R_G=2.0\Omega, V_{GE}=\pm 15\text{V}, T_j=25^{\circ}\text{C}$		150		ns
t_r	Rise Time			30		ns
$t_{d(off)}$	Turn-Off Delay Time			272		ns
t_f	Fall Time			48		ns
E_{on}	Turn-On Switching Loss			1.00		mJ
E_{off}	Turn-Off Switching Loss			4.52		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}, R_G=2.0\Omega, V_{GE}=\pm 15\text{V}, T_j=125^{\circ}\text{C}$		160		ns
t_r	Rise Time			40		ns
$t_{d(off)}$	Turn-Off Delay Time			296		ns
t_f	Fall Time			56		ns
E_{on}	Turn-On Switching Loss			1.55		mJ
E_{off}	Turn-Off Switching Loss			5.36		mJ
$t_{d(on)}$	Turn-On Delay Time	$V_{CC}=300\text{V}, I_C=200\text{A}, R_G=2.0\Omega, V_{GE}=\pm 15\text{V}, T_j=150^{\circ}\text{C}$		170		ns
t_r	Rise Time			40		ns
$t_{d(off)}$	Turn-Off Delay Time			304		ns
t_f	Fall Time			56		ns
E_{on}	Turn-On Switching Loss			1.80		mJ
E_{off}	Turn-Off Switching Loss			5.52		mJ
I_{SC}	SC Data	$t_p \leq 6\mu\text{s}, V_{GE}=15\text{V}, T_j=150^{\circ}\text{C}, V_{CC}=360\text{V}, V_{CEM} \leq 650\text{V}$		1000		A

Diode Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
V_F	Diode Forward Voltage	$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=25^{\circ}\text{C}$		1.55	2.00	V
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=125^{\circ}\text{C}$		1.50		
		$I_F=200\text{A}, V_{GE}=0\text{V}, T_j=150^{\circ}\text{C}$		1.45		
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=200\text{A},$ $-di/dt=5700\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=25^{\circ}\text{C}$		10.0		μC
I_{RM}	Peak Reverse Recovery Current			160		A
E_{rec}	Reverse Recovery Energy			3.00		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=200\text{A},$ $-di/dt=5700\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=125^{\circ}\text{C}$		17.0		μC
I_{RM}	Peak Reverse Recovery Current			230		A
E_{rec}	Reverse Recovery Energy			5.20		mJ
Q_r	Recovered Charge	$V_R=300\text{V}, I_F=200\text{A},$ $-di/dt=5700\text{A}/\mu\text{s}, V_{GE}=-15\text{V}$ $T_j=150^{\circ}\text{C}$		20.0		μC
I_{RM}	Peak Reverse Recovery Current			240		A
E_{rec}	Reverse Recovery Energy			5.80		mJ

Module Characteristics $T_C=25^{\circ}\text{C}$ unless otherwise noted

Symbol	Parameter	Min.	Typ.	Max.	Unit
L_{CE}	Stray Inductance			20	nH
$R_{CC'+EE'}$	Module Lead Resistance, Terminal to Chip		0.35		m Ω
R_{thJC}	Junction-to-Case (per IGBT)			0.245	K/W
	Junction-to-Case (per Diode)			0.451	
R_{thCH}	Case-to-Heatsink (per IGBT)		0.031		K/W
	Case-to-Heatsink (per Diode)		0.057		
	Case-to-Heatsink (per Module)		0.010		
M	Terminal Connection Torque, Screw M6	2.5		5.0	N.m
	Mounting Torque, Screw M6	3.0		5.0	
G	Weight of Module		300		g

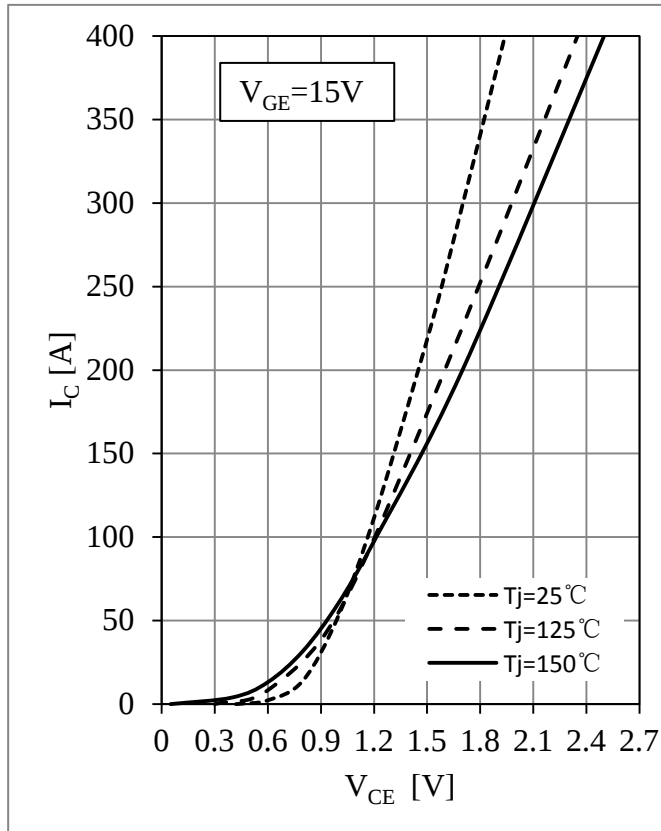


Fig 1. IGBT Output Characteristics

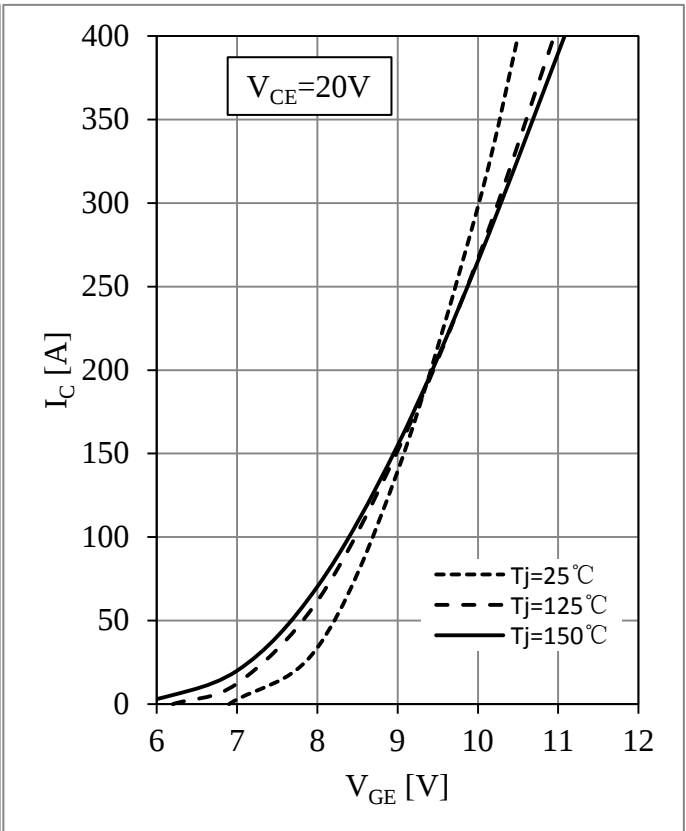
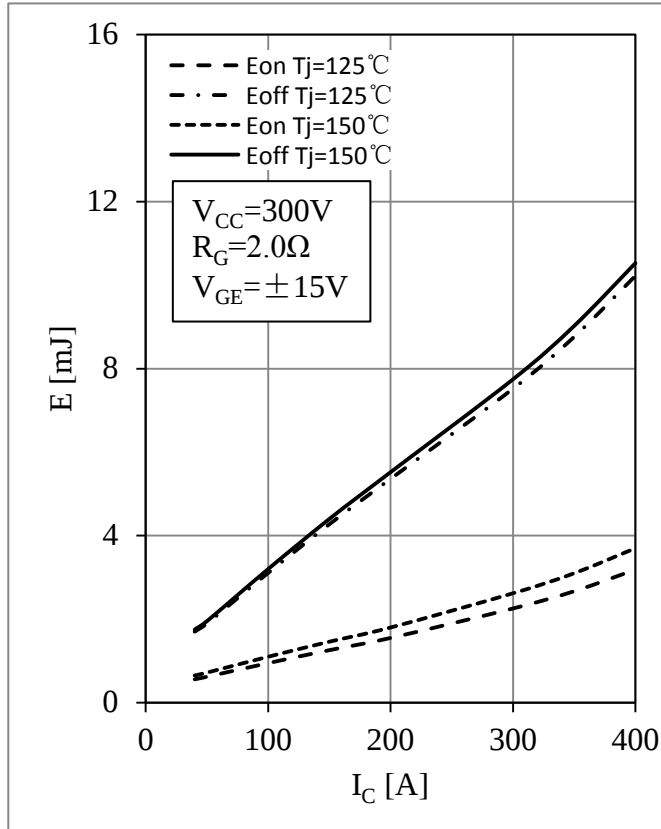
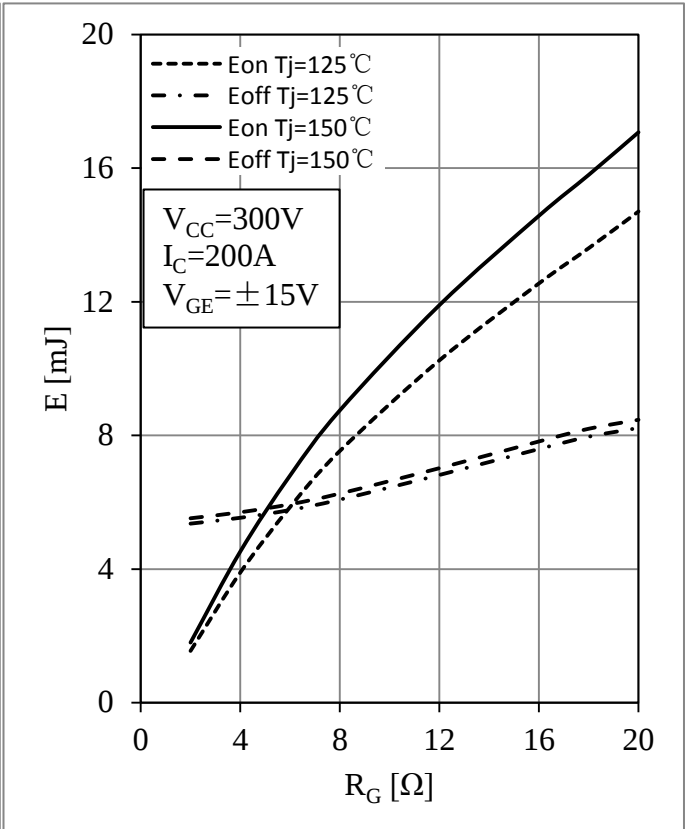


Fig 2. IGBT Transfer Characteristics

Fig 3. IGBT Switching Loss vs. I_C Fig 4. IGBT Switching Loss vs. R_G

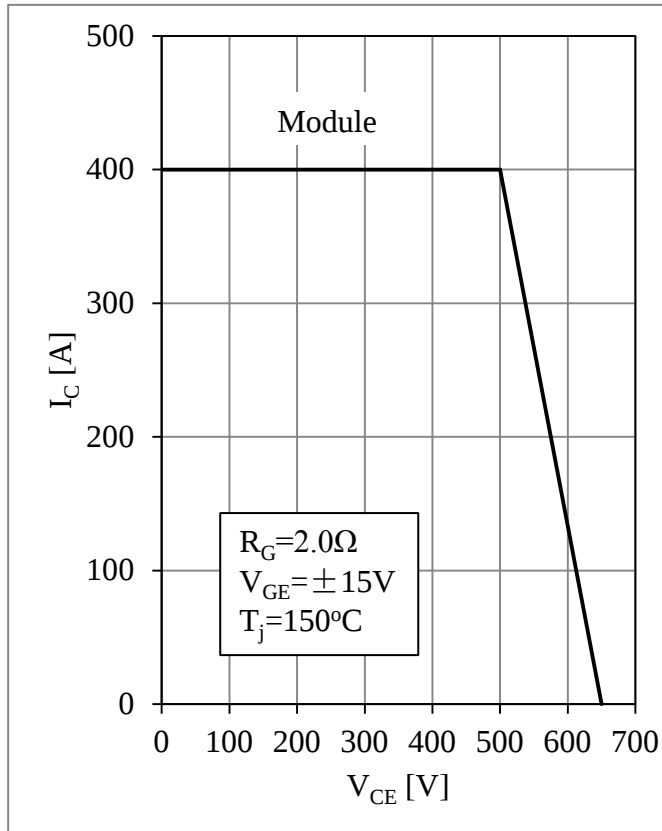


Fig 5. RBSOA

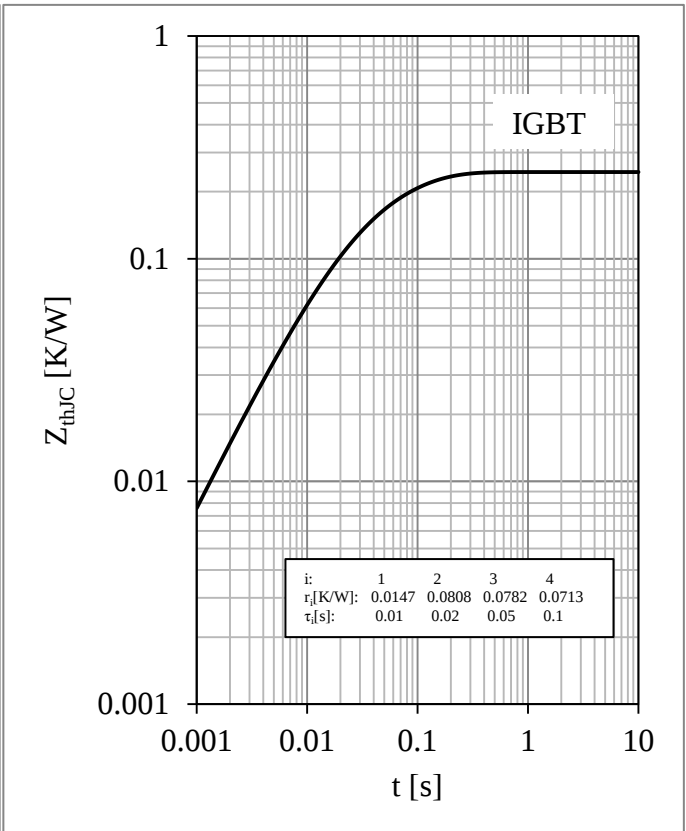


Fig 6. IGBT Transient Thermal Impedance

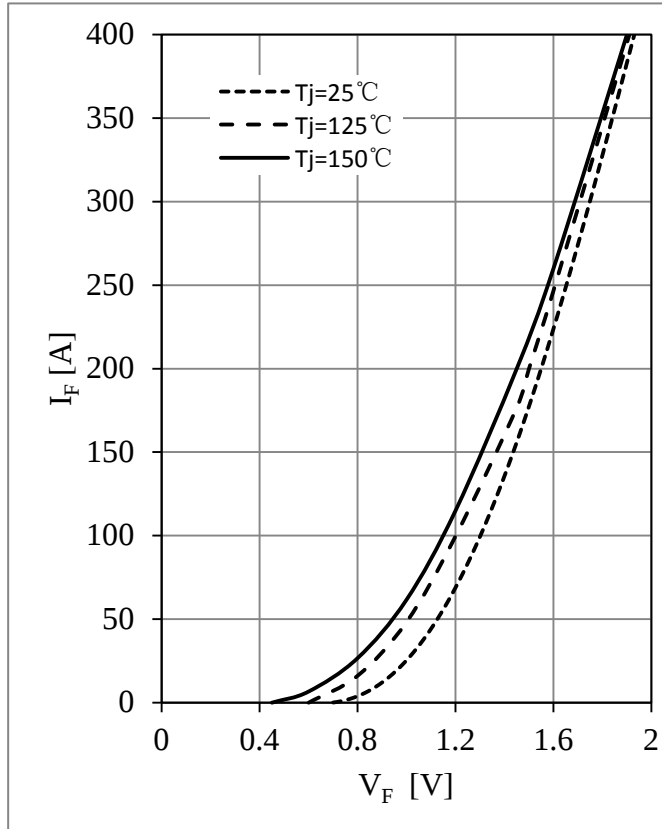
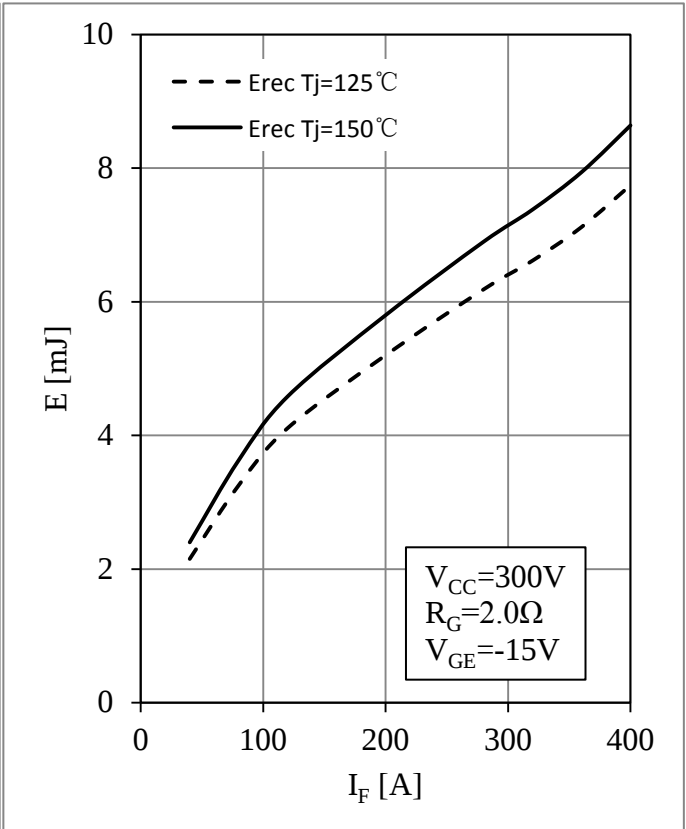


Fig 7. Diode Forward Characteristics

Fig 8. Diode Switching Loss vs. I_F

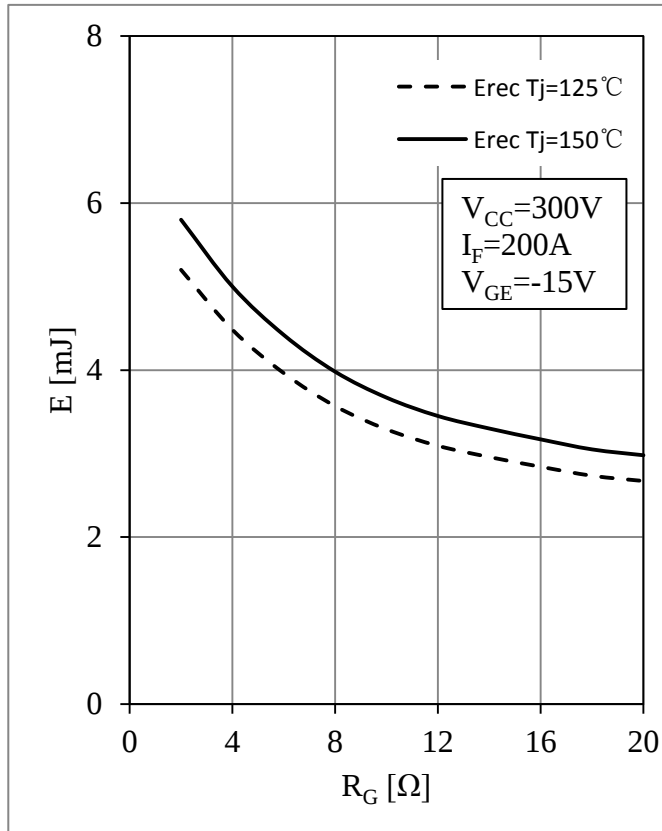
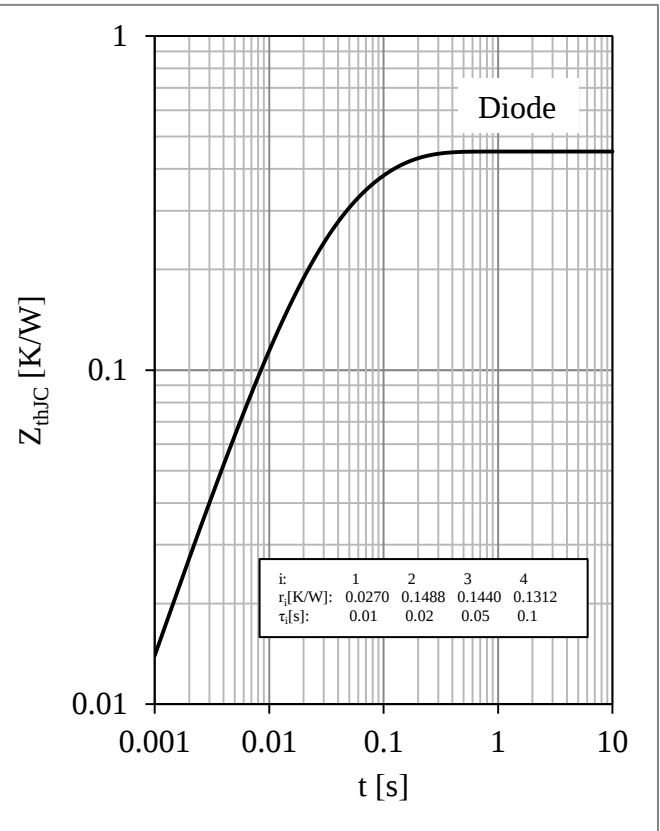
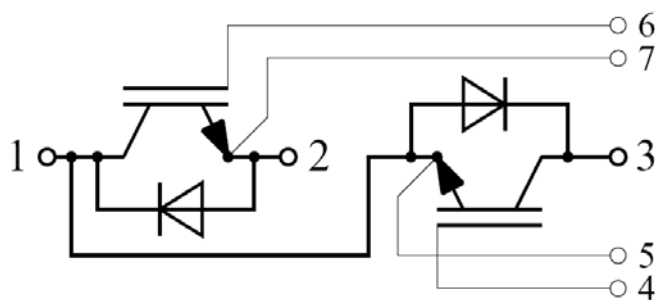
Fig 9. Diode Switching Loss vs. R_G 

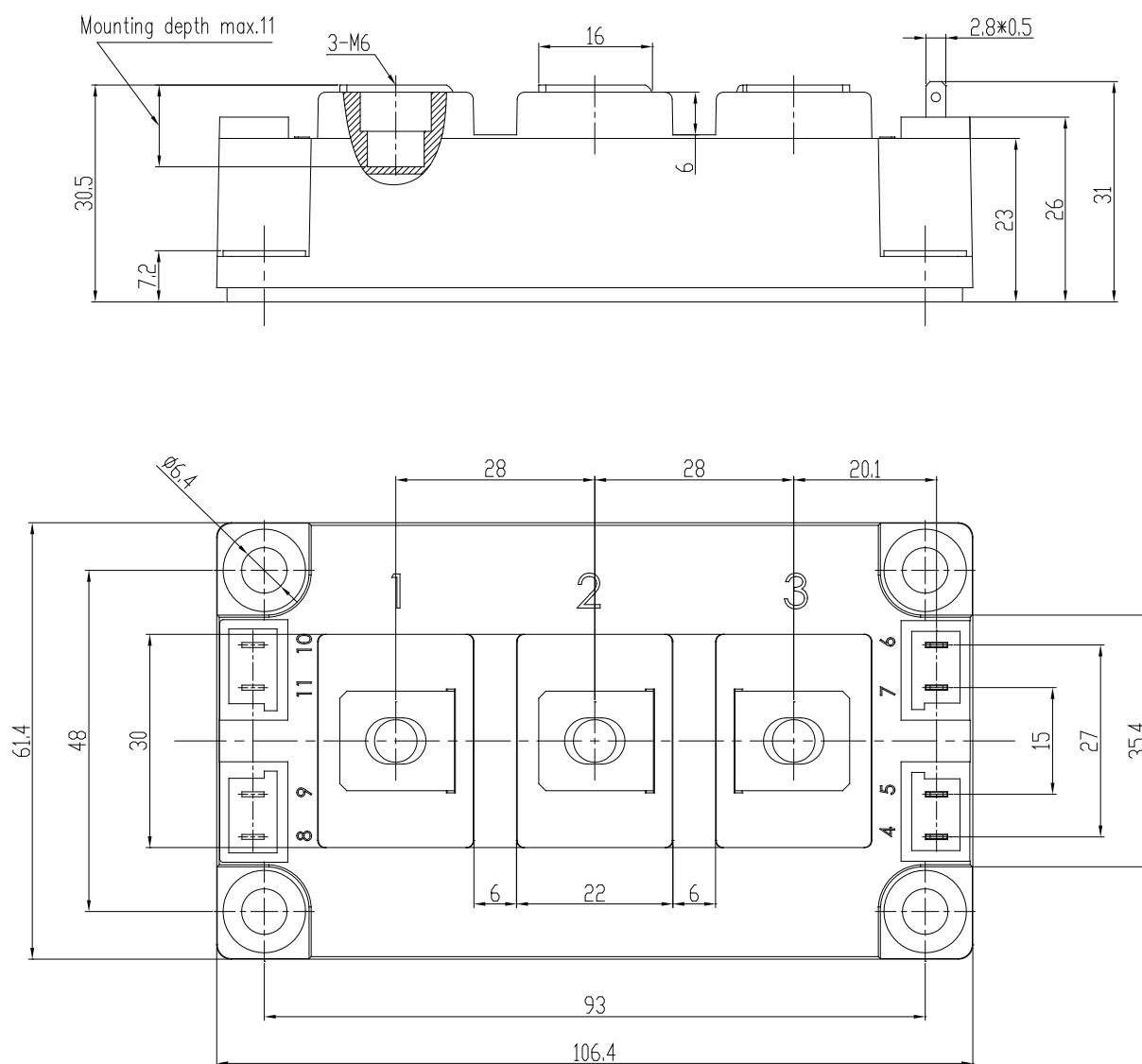
Fig 10. Diode Transient Thermal Impedance

Circuit Schematic



Package Dimensions

Dimensions in Millimeters



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